

3 相无刷电机驱动器

查询样片: **DRV3203E-Q1**

特性

- 符合汽车应用要求
- 具有符合 **AEC-Q100** 的下列结果:
 - 器件温度 **0 级**: **-40° 至 150°** 的环境运行温度范围
 - 器件人体模型 (**HBM**) 静电放电 (**ESD**) 分类等级 **H2**
 - 器件充电器件模型 (**CDM**) **ESD** 分类等级 **C2**
- 针对 **N 通道金属氧化物半导体 (MOS)** 场效应晶体管 (**MOSFET**) 的 **3 相预驱动器**
- 脉宽调制 (**PWM**) 频率高达 **20kHz**
- 故障诊断
- 电荷泵
- 相位比较器
- 微控制器 (**MCU**) 复位发生器
- 串行端口/接口 (**SPI**)
- 电机电流感测
- **3.3V** 稳压器
- 低电流睡眠模式
- 运行 **VB** 范围从 **5.3V 至 26.5 V**
- **48 引脚 PHP** 封装

应用范围

- 汽车电机控制应用
 - 油泵
 - 燃料泵
 - 水泵

说明

DRV3203E-Q1 器件是一款设计用于诸如油泵或水泵等 3 相电机控制应用的场效应晶体管 (FET) 预驱动器。此器件具有 3 个高侧预 FET 驱动器和 3 个低侧驱动器, 这些驱动器由一个外部 MCU 控制。一个电荷泵为高侧供电, 并且无需自举电容器。为了实现整流, 这个集成电路 (IC) 发送一个条件电机信号并输出至 MCU。提供欠压、过压、过流、过热和整流桥故障诊断。用户能够使用一个电池共模范围内的集成电流感测放大器和比较器来测量此电机电流, 这样可以使得电机电流用于高侧电流感测应用中。外部电阻器设定此增益。用户可以通过 SPI 来配置预驱动器和其它内部设置。

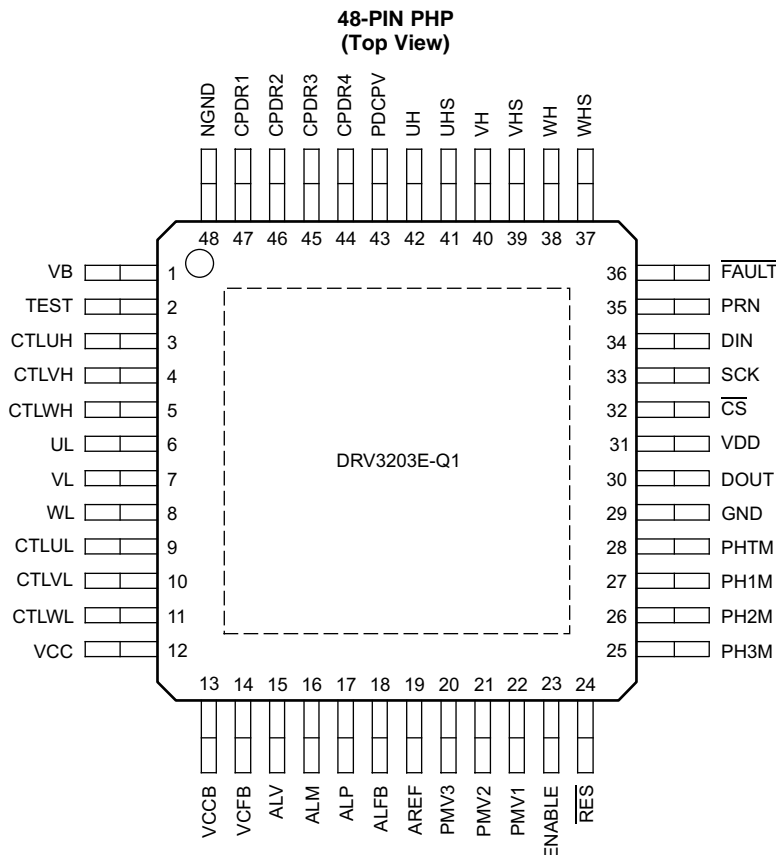


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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

DEVICE INFORMATION



PIN FUNCTIONS

PIN		TYPE	MAXIMUM RATING	FUNCTION
NAME	NO.			
ALFB	18	O	−0.3 V to 40 V	Motor current-sense amplifier feedback
ALM	16	I	−0.3 V to 40 V	Motor current- sense amplifier negative input
ALP	17	I	−0.3 V to 40 V	Motor current- sense amplifier positive input
ALV	15	O	−0.3 V to 3.6 V	Motor current- sense amplifier output
AREF	19	O	−0.3 V to 40 V	Reference output of motor current- sense amplifier
CPDR1	47	O	−0.3 V to 40 V	Charge-pump output
CPDR2	46	O	−0.3 V to 40 V	Charge- pump output
CPDR3	45	O	−0.3 V to 40 V	Charge- pump output
CPDR4	44	O	−0.3 V to 40 V	Charge- pump output
CS	32	I	−0.3 V to 3.6 V	SPI chip select
CTLUH	3	I	−0.3 V to 3.6 V	Pre-driver parallel input
CTLUL	9	I	−0.3 V to 3.6 V	Pre-driver parallel input
CTLVH	4	I	−0.3 V to 3.6 V	Pre-driver parallel input
CTLVL	10	I	−0.3 V to 3.6 V	Pre-driver parallel input
CTLWH	5	I	−0.3 V to 3.6 V	Pre-driver parallel input
CTLWL	11	I	−0.3 V to 3.6 V	Pre-driver parallel input

PIN FUNCTIONS (continued)

PIN		TYPE	MAXIMUM RATING	FUNCTION
NAME	NO.			
DIN	34	I	–0.3 V to 3.6 V	SPI data input
DOUT	30	O	–0.3 V to 3.6 V	SPI data output
ENABLE	23	I	–0.3 V to 40 V	Enable input
$\overline{\text{FAULT}}$	36	O	–0.3 V to 3.6 V	Diagnosis output
GND	29	I	–0.3 V to 0.3 V	GND
NGND	48	I	–0.3 V to 0.3 V	Power GND
PDCPV	43	O	–0.3 V to 40 V	Charge pump output
PH1M	27	I	–1 V to 40 V	Phase comparator input
PH2M	26	I	–1 V to 40 V	Phase comparator input
PH3M	25	I	–1 V to 40 V	Phase comparator input
PHTM	28	I	–1 V to 40 V	Phase comparator reference input
PMV1	22	O	–0.3 V to 3.6 V	Phase comparator output
PMV2	21	O	–0.3 V to 3.6 V	Phase comparator output
PMV3	20	O	–0.3 V to 3.6 V	Phase comparator output
PRN	35	I	–0.3 V to 3.6 V	Watchdog timer-pulse input
$\overline{\text{RES}}$	24	O	–0.3 V to 3.6 V	MCU reset output
SCK	33	I	–0.3 V to 3.6 V	SPI clock
TEST	2	I	–0.3 V to 20 V	TEST input
UH	42	O	–5 V to 40 V	Pre-driver output
UHS	41	O	–5 V to 40 V	Pre-driver reference
UL	6	O	–0.3 V to 20 V	Pre-driver output
VB	1	I	–0.3 V to 40 V	VB input
VCC	12	I	–0.3 V to 3.6 V	VCC supply input
VCCB	13	O	–0.3 V to 40 V	VCC regulator base driver of PNP external transistor
VCFB	14	I	–0.3 V to 40 V	VCC regulator current-sense input
VDD	31	O	–0.3 V to 3.6 V	VDD supply output
VH	40	O	–5 V to 40 V	Pre-driver output
VHS	39	O	–5 V to 40 V	Pre-driver reference
VL	7	O	–0.3 V to 20 V	Pre-driver output
WH	38	O	–5 V to 40 V	Pre-driver output
WHS	37	O	–5 V to 40 V	Pre-driver reference
WL	8	O	–0.3 V to 20 V	Pre-driver output

BLOCK DIAGRAM

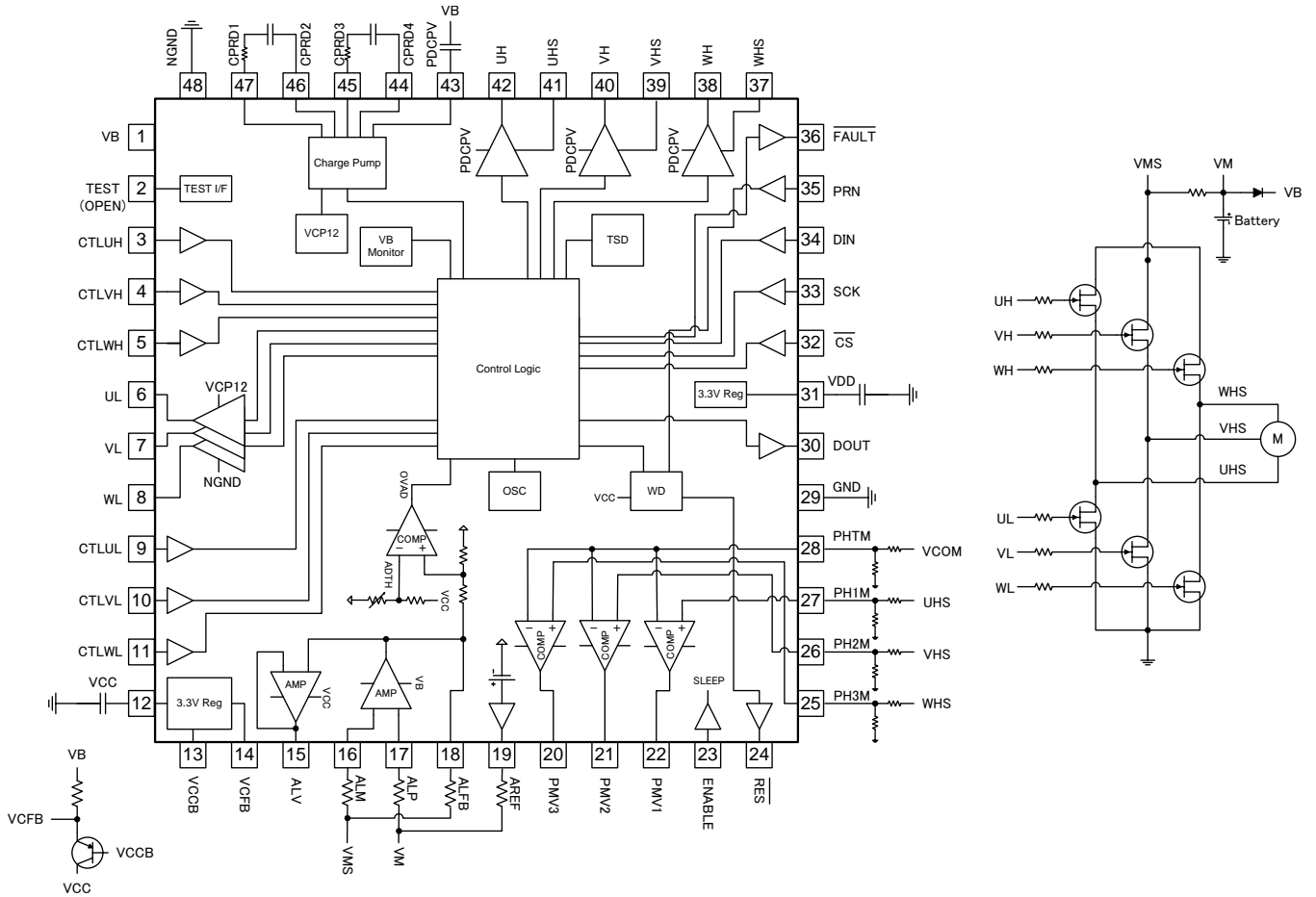


Figure 1. Top Block Diagram

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT	
ESD⁽¹⁾					
ESD all pins	ESD performance of all pins to any other pin	HBM model	-2	2	kV
		CDM model	-500	500	V
TEMPERATURE					
T _A	Operating temperature range		-40	150	°C
T _J	Junction temperature		-40	175	°C
T _{stg}	Storage temperature		-55	175	°C

(1) Performance of ESD testing is according to the ACE-Q100 standard.

THERMAL INFORMATION

THERMAL METRIC ⁽¹⁾		DRV3203E-Q1		UNIT
		PHP		
		48 PINS		
θ _{JA}	Junction-to-ambient thermal resistance ⁽²⁾	26.1		°C/W
θ _{JCtop}	Junction-to-case (top) thermal resistance ⁽³⁾	11.5		°C/W
θ _{JB}	Junction-to-board thermal resistance ⁽⁴⁾	7.2		°C/W
ψ _{JT}	Junction-to-top characterization parameter ⁽⁵⁾	0.2		°C/W
ψ _{JB}	Junction-to-board characterization parameter ⁽⁶⁾	7.1		°C/W
θ _{JCbot}	Junction-to-case (bottom) thermal resistance ⁽⁷⁾	0.4		°C/W

- For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).
- The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
- The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
- The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
- The junction-to-top characterization parameter, ψ_{JT}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA}, using a procedure described in JESD51-2a (sections 6 and 7).
- The junction-to-board characterization parameter, ψ_{JB}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA}, using a procedure described in JESD51-2a (sections 6 and 7).
- The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

SUPPLY VOLTAGE AND CURRENT

V_B = 12 V, T_A = -40°C to +150°C (unless otherwise specified)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
SUPPLY INPUT						
VB1 ⁽¹⁾	VB supply voltage (motor operation)	Full device functionality	5.3	12	18	V
VB2 ⁽¹⁾	VB supply voltage (MCU operation)	Full device functionality	4.5	12	18	V
VB3 ⁽²⁾	VB supply voltage		18	-	26.5	V
I _{vb}	VB operating current	ENABLE = High, no PWM	-	18	27	mA
I _{vbq}	VB quiescent current	ENABLE = Low	-	50	100	µA

- Performance of supply voltage 5.3 to 18 V is according to the ACE-Q100 (Grade 0) standard.
- Specified by design.

DETAILED DESCRIPTION

WATCHDOG

Description:

A watchdog monitors the PRN signal and VCC supply level and generates a reset to the MCU through the $\overline{\text{RES}}$ pin if the status of PRN is not normal or VCC is lower than the specified threshold level. Detection of a special pattern on the PRN input during power up can disable the watchdog.

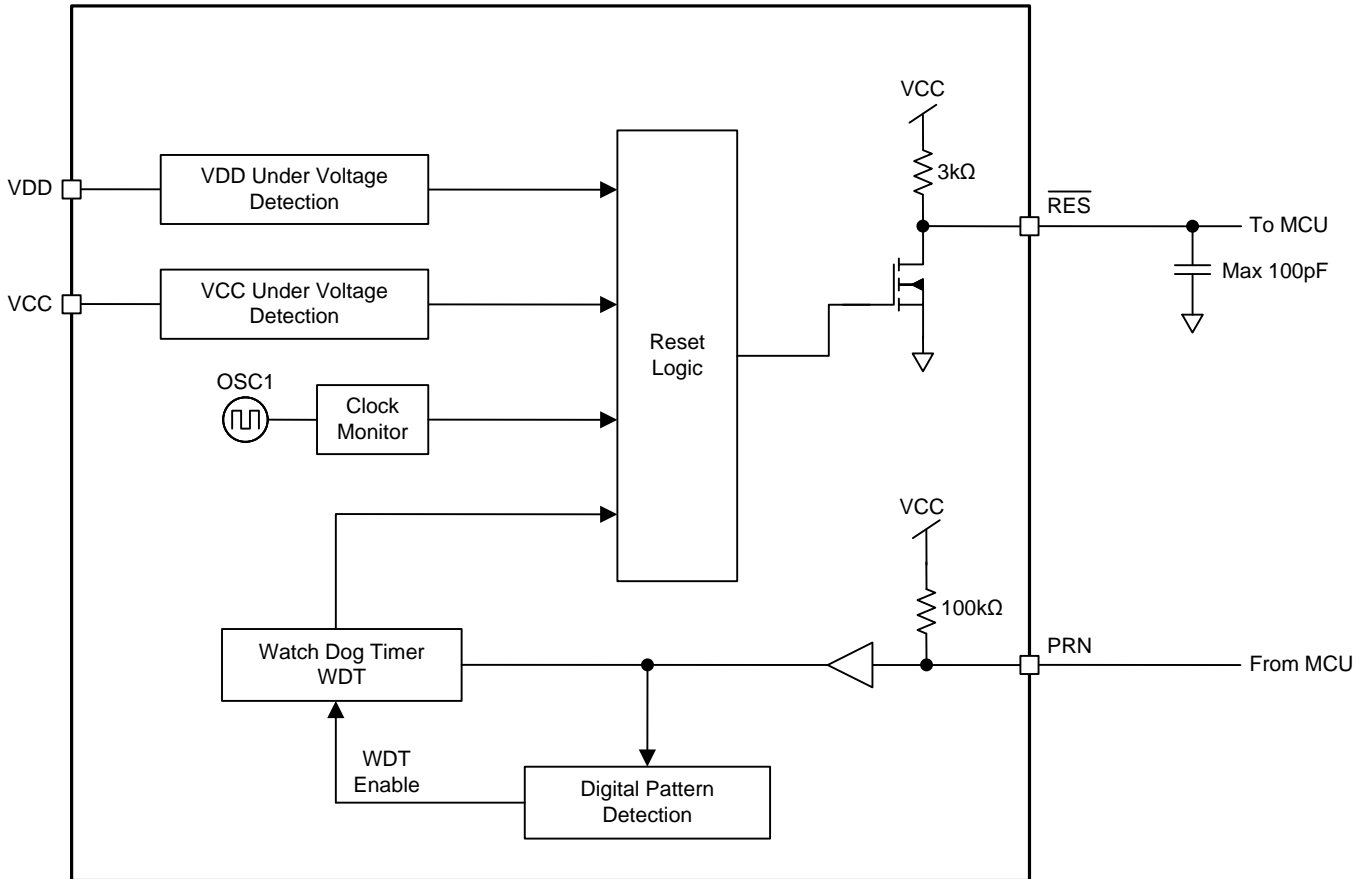
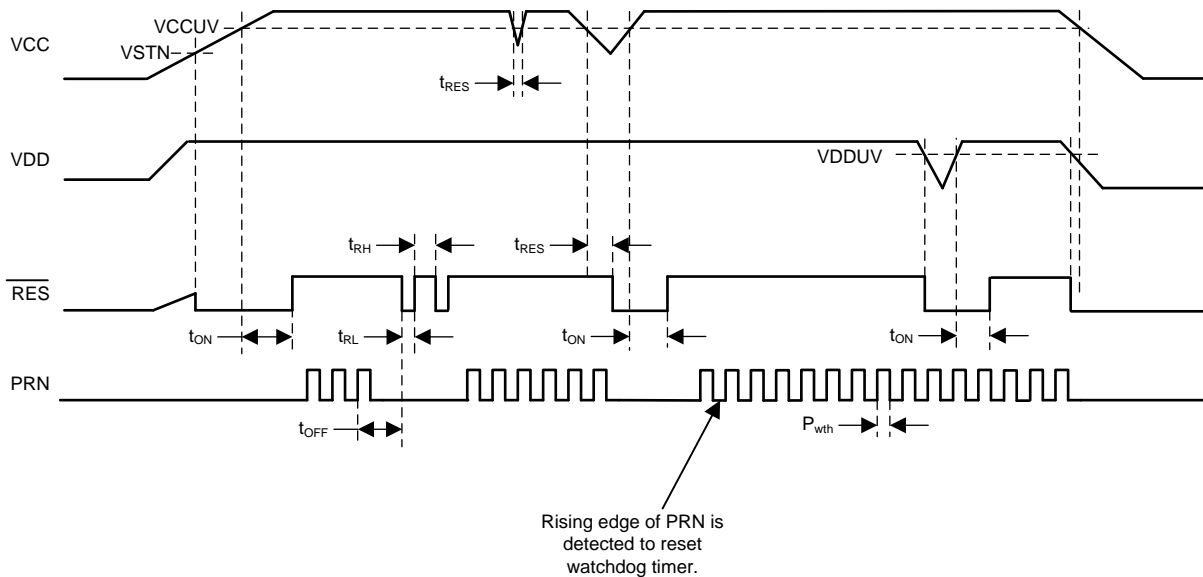


Figure 2. Watchdog Block Diagram



NOTE: VCC undervoltage condition sets $\overline{\text{RES}}$ = Low.

Figure 3. Watchdog Timing Chart

Table 1. WATCHDOG ELECTRICAL CHARACTERISTICS⁽¹⁾

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
VB = 12 V, TA = -40°C to +150°C (unless otherwise specified)						
WATCHDOG						
VSTN ⁽²⁾	Function start VCC voltage $\overline{\text{RES}}$	See Figure 3	-	0.8	1.3	V
t _{ON} ⁽²⁾	Power-on time $\overline{\text{RES}}$		2.5	3	3.5	ms
t _{OFF} ⁽²⁾	Clock-off reset time $\overline{\text{RES}}$		64	80	96	ms
t _{RL} ⁽²⁾	Reset-pulse low time $\overline{\text{RES}}$		16	20	24	ms
t _{RH} ⁽²⁾	Reset-pulse high time $\overline{\text{RES}}$		64	80	96	ms
t _{RES} ⁽²⁾	Reset delay time $\overline{\text{RES}}$		30	71.5	90	μs
P _{wth} ⁽²⁾	Pulse duration PRN		2	-	-	μs

(1) The timing parameters are invalid if watch dog timer is disabled.
 (2) Specified by design.

SERIAL PORT I/F

Description:

Setting device configuration and reading out diagnostic information is via SPI. SPI operates in slave mode. SPI uses four signals according to the timing chart of [Figure 5](#).

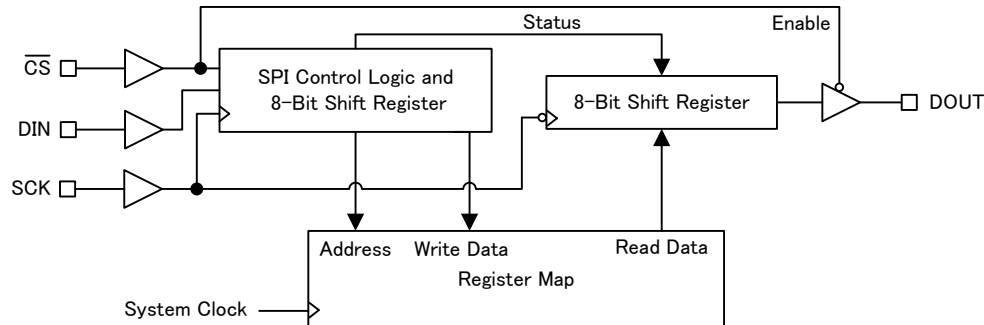


Figure 4. Block Diagram of SPI

\overline{CS} - Chip Select

The MCU uses \overline{CS} to select the IC. \overline{CS} is normally high, and communication is possible only when it is forced low. When \overline{CS} falls, communication between the IC and the MCU starts. The transmitted data are latched and the DOUT output pin leaves high impedance. When \overline{CS} rises, communication stops. The DOUT output pin goes into high impedance. The next falling edge starts another communication. There is a minimum waiting time between the two communications (t_{wait}). The pin has an internal pullup.

SCK - Synchronization Serial Clock

The MCU uses SCK to synchronize communication. SCK is normally low, and the valid clock-pulse number is 16. At each falling edge, the MCU writes a new bit on the DIN input, and this IC writes a new bit on the DOUT output pin. At each rising edge, this IC reads the new bit on DIN, and the MCU reads the new bit on DOUT. The maximum clock frequency is 4 MHz. The pin has an internal pulldown.

DIN - Serial Input Data

DIN receives 16-bit data. The order of received bits is from the MSB (first) to the LSB (last). The pin has an internal pulldown. Update of the internal register with the received bits occurs only if the number of clock pulses is 16 while \overline{CS} is low.

DOUT - Serial Output Data

DOUT transmits 16-bit data. It is a three-state output, and it is in the high-impedance state when \overline{CS} is high. The order of serial data-bit transmission is from the MSB (first) to the LSB (last).

SPI ELECTRICAL CHARACTERISTICS

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
VB = 12 V, T_A = -40°C to +150°C (unless otherwise specified)						
SPI						
f _{op}	SPI clock frequency		-	4	MHz	
t _{lead} ⁽¹⁾	Enable lead time	200	-	-	ns	
t _{wait} ⁽¹⁾	Wait time between two successive communications	5	-	-	µs	
t _{lag} ⁽¹⁾	Enable lag time	100	-	-	ns	
t _{pw} ⁽¹⁾	SCLK pulse duration	100	-	-	ns	
t _{su} ⁽¹⁾	Data setup time	100	-	-	ns	
t _h ⁽¹⁾	Data hold time	100	-	-	ns	
t _{dis} ⁽¹⁾	Data-output disable time	-	-	200	ns	
t _{en} ⁽¹⁾	Data-output enable time	-	-	100	ns	
t _d ⁽¹⁾	Data delay time, SCK to DOUT	C _L = 50 pF, see Figure 5.	0	-	100	ns

(1) Specified by design.

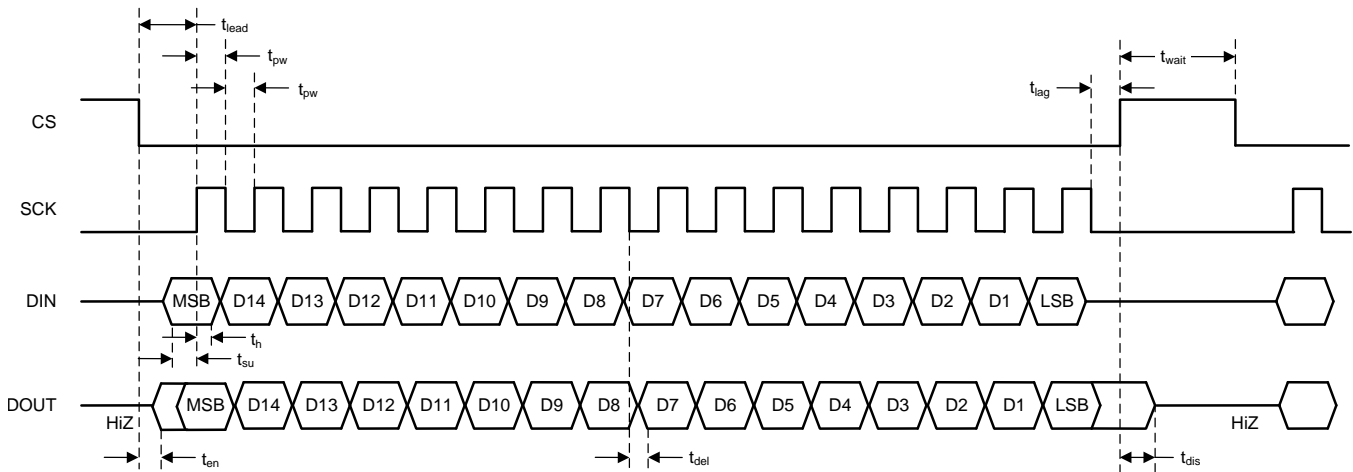


Figure 5. SPI Timing Diagram

Table 2. SPI Serial Input Format

	MSB	D14	D13	D12	D11	D10	D9	D8
DIN	RW[1]	RW[0]	Addr[5]	Addr[4]	Addr[3]	Addr[2]	Addr[1]	Addr[0]
	D7	D6	D5	D4	D3	D2	D1	LSB
DIN	Data[7]	Data[6]	Data[5]	Data[4]	Data[3]	Data[2]	Data[1]	Data[0]

Table 3. SPI Serial Output Data Format

	MSB	D14	D13	D12	D11	D10	D9	D8
DOUT	0	Frame fault	0	0	0	0	0	1
	D7	D6	D5	D4	D3	D2	D1	LSB
DOUT	Data[7]	Data[6]	Data[5]	Data[4]	Data[3]	Data[2]	Data[1]	Data[0]

SPI serial input and output format

RW[1:0] : 01: write mode; 00: read mode

Addr[5:0] : Address of SPI access

Data[7:0] : Input data to write or output data to read

Frame fault : 0: No error exists in the previous SPI frame.
 : 1: Error exists in the previous SPI frame.

Table 4. SPI Register Map

Register Name	Addr (Hex)	b7	b6	b5	b4	b3	b2	b1	b0	Reset (Hex)	
Reserved	00	RSVD								00	
CFGUNLK	01	RSVD				CFGUNLK					00
FLTCFG	02	FLGLATCH_EN	MTOCTH			RSVD	VCCUVTH	VBUVTH			00
Reserved	03	RSVD								00	
FLTEN0	04	FE_MTOC	FE_VCCOC	FE_VCCOV	FE_VDDOV	FE_CPOV	FE_CPUV	FE_VBOV	FE_VBUV	FF	
FLTEN1	05	RSVD								FE_TSD	01
SDNEN0	06	SE_MTOC	SE_VCCOC	SE_VCCOV	SE_VDDOV	SE_CPOV	SE_CPUV	SE_VBOV	SE_VBUV	FF	
SDNEN1	07	RSVD								SE_TSD	01
FLTFLG0	08	MTOC	VCCOC	VCCOV	VDDOV	CPOV	CPUV	VBOV	VBUV	00	
FLTFLG1	09	RSVD								TSD	00
CSCFG	0A	RSVD					CSOFFSET				00
PDCFG	0B	RSVD						DEADT			00
DIAG	0C	RSVD					VCCUVRST	WDTRST	CMRST		00
SPARE	0D	SPARE						SEL_COMP_HYS			00
Reserved	0E-3F	RSVD								00	

Register Descriptions

Access type: R = Read and W = Write.

Reserved register: Read of reserved bits return 0 and write has no effect.

CFGUNLK (address 0x01): Configuration Unlock Register

Bit	Name	Type	Reset	Description
3:0	CFGUNLK	RW	0000	DRV3203E-Q1 SPI register map has lock and unlock mode, and it is in lock mode by default. MCU can write values of the following registers in unlock mode; <ul style="list-style-type: none"> • FLTCFG • FLTEN0 and FLTEN1 • SDNEN0 and SDNEN1 • CSCFG • PDCFG • WDCFG In lock mode, read returns the values, but writing the registers have no effect. Device enters unlock mode by writing 0x5, 0x8, 0x7 to CFGUNLK register in series. Device exits from unlock mode by writing 0x0.

FLTCFG (address 0x02): Fault Detection Configuration Register

Bit	Name	Type	Reset	Description
7	FLGLATCH_EN	RW	0	Fault-flag (FLTFLG*) latch enable 0: Fault events do not latch fault-flag register bits. 1: Latching of fault-flag register bits by the fault events occurs. The flag bits remain asserted until cleared.
6:4	MTOCTH	RW	000	Motor overcurrent detection threshold (ADTH) 000: 1.32 V 001: 1.65 V 010: 1.98 V 011: 2.31 V 100: 2.64 V Others: 1.32 V
3	RSVD	R	0	Reserved
2	VCCUVTH	RW	0	VCC undervoltage detection threshold 0: 2.2 V 1: 2.4 V
1:0	VBUVTH	RW	00	VB undervoltage detection threshold 00: 4 V 01: 4.5 V 10: 5 V 11: 5.5 V

FLTEN0 (address 0x04): FAULT Pin Enable Register 0

Bit	Name	Type	Reset	Description
7	FE_MTOC	RW	1	FAULT pin enable of FLTFLG0 register bits. 0: Assertion of the FAULT pin does not occur when the fault flag bit is 1 1: Assertion of the FAULT pin to low level occurs when the fault flag bit is 1. See Figure 6
6	FE_VCCOC	RW	1	
5	FE_VCCOV	RW	1	
4	FE_VDDOV	RW	1	
3	FE_CPOV	RW	1	
2	FE_CPUV	RW	1	
1	FE_VBOV	RW	1	
0	FE_VBUV	RW	1	

FLTEN1 (address 0x05): FAULT Pin Enable Register 1

Bit	Name	Type	Reset	Description
7:1	RSVD	R	0000 000	Reserved
0	FE_TSD	RW	1	FAULT pin enable of TSD flag bit 0: Assertion of the FAULT pin does not occur when the fault flag bit is 1 1: Assertion of the FAULT pin to low level occurs when the TSD flag bit is 1. See Figure 6

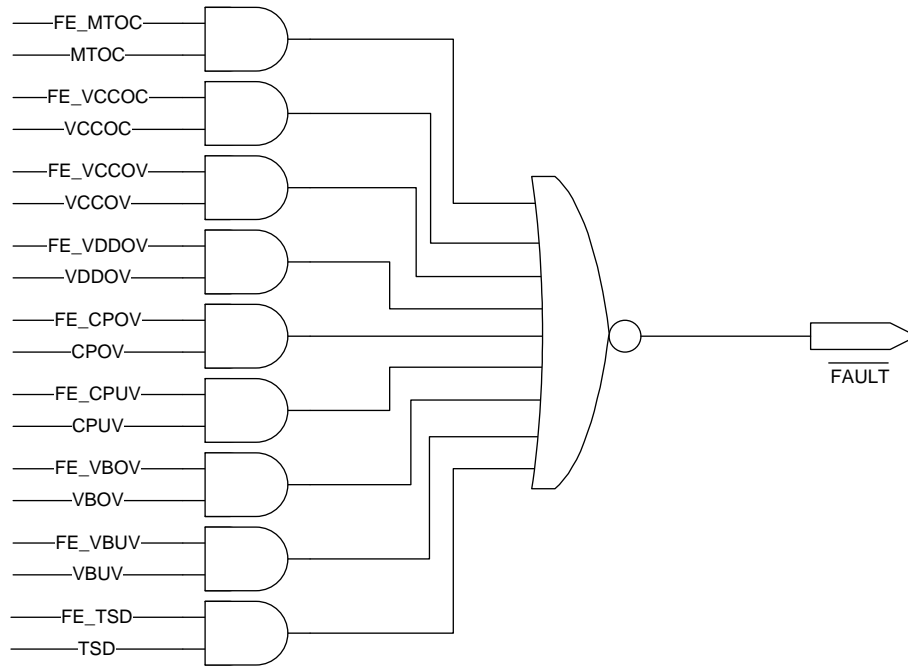


Figure 6. $\overline{\text{FAULT}}$ Pin Enable Logic

SDNEN0 (address 0x06): Pre-Driver Shutdown Enable Register 0

Bit	Name	Type	Reset	Description
7	SE_MTOC	RW	1	Pre-driver shutdown enable of FLTFLG0 register bits 0: Disabling of the pre-driver outputs does not occur when the fault flag bit is 1. 1: Disabling of the pre-driver outputs occurs when the fault flag bit is 1. Both the high-side and low-side FETs turn off. See Figure 7 .
6	SE_VCCOC	RW	1	
5	SE_VCCOV	RW	1	
4	SE_VDDOV	RW	1	
3	SE_CPOV	RW	1	
2	SE_CPUV	RW	1	
1	SE_VBOV	RW	1	
0	SE_VBUV	RW	1	

SDNEN1 (address 0x07): Pre-Driver Shutdown Enable Register 1

Bit	Name	Type	Reset	Description
7:1	RSVD	R	0000 000	Reserved
0	SE_TSD	RW	1	Pre-driver shutdown enable of TSD flag bits 0: Disabling of the pre-driver outputs does not occur when the TSD flag bit is 1. 1: Disabling of the pre-driver outputs occurs when the TSD flag bit is 1. Both the high-side and low-side FETs turn off. See Figure 7 .

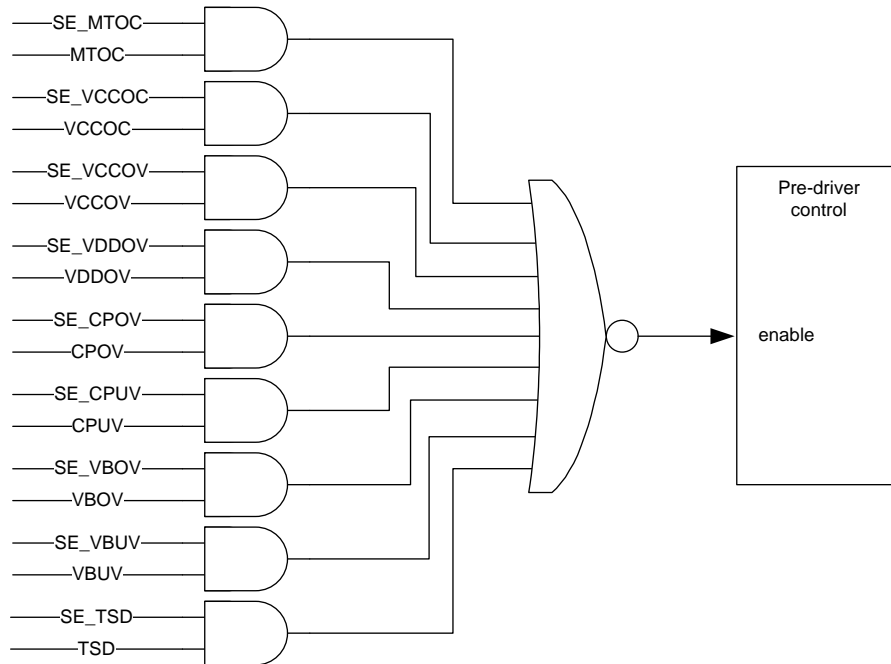


Figure 7. Pre-Driver Shutdown Logic

FLTLFG0 (address 0x08): Fault Flag Register 0

Bit	Name	Type ⁽¹⁾	Reset	Description
				Fault flag bits of the following conditions; ⁽²⁾
7	MTOC	RW	0	MTOC: Motor overcurrent. (OVAD)
6	VCCOC	RW	0	VCCOC: VCC overcurrent
5	VCCOV	RW	0	VCCOV: VCC overvoltage
4	VDDOV	RW	0	VDDOV: VDD overvoltage
3	CPOV	RW	0	CPOV: Charge-pump overvoltage
2	CPUV	RW	0	CPUV: Charge-pump undervoltage
1	VBOV	RW	0	VBOV: VB overvoltage
0	VBUV	RW	0	VBUV: VB undervoltage
				If FLTCFG.FLGLATCH_EN = 1
				0: Read = No fault condition exists since last cleared. Write = No effect
				1: Read = Fault condition exists. Write = Clear the flag.
				If FLTCFG.FLGLATCH_EN = 0
				0: Read = No fault condition Write = No effect
				1: Read = Fault condition Write = No effect

(1) R: Read, W: Write

(2) Assertion of the fault flags may occur during power up.

FLGFLT1 (address 0x09): Fault Flag Register 1

Bit	Name	Type ⁽¹⁾	Reset	Description
7:1	RSVD	R	0000 000	Reserved
0	VBUV	RW	1	Fault flag bit of thermal shutdown condition. ⁽²⁾ If FLTCFG.FLGLATCH_EN = 1 0: Read = No fault condition exists since last cleared. Write = No effect 1: Read = Fault condition exists. Write = Clear the flag If FLTCFG.FLGLATCH_EN = 0 0: Read = No fault condition Write = No effect 1: Read = Fault condition Write = No effect

- (1) R: Read, W: Write
- (2) Assertion of the fault flags may occur during power up.

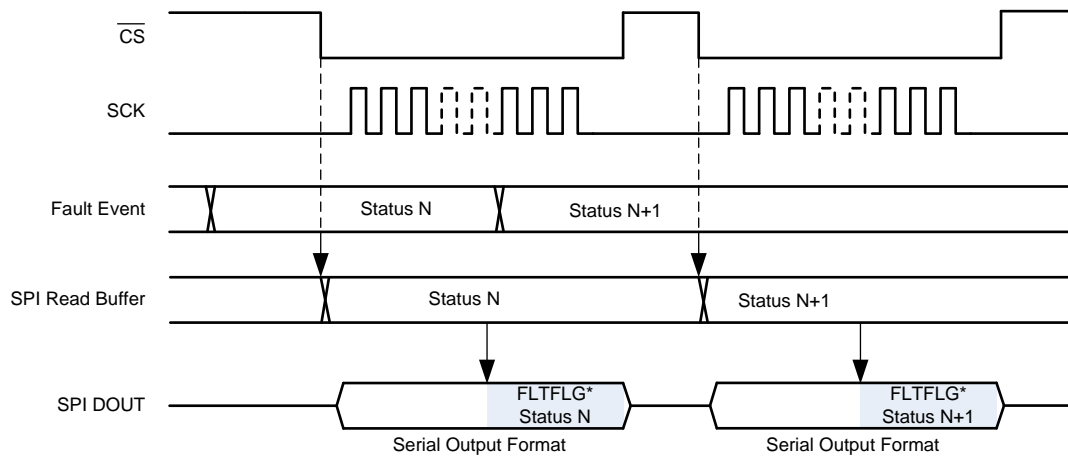
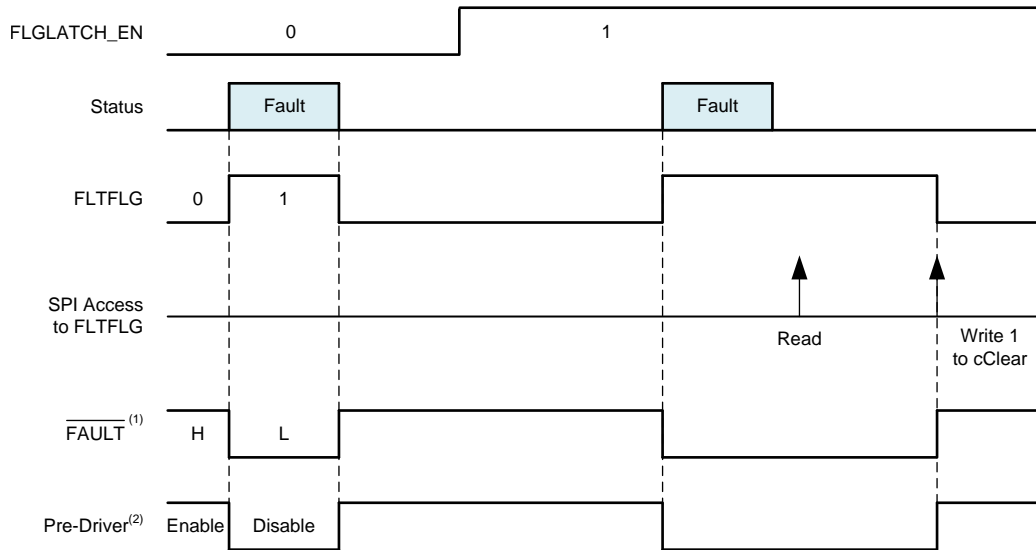


Figure 8. SPI Data-Out Timing Chart of Fault Flag Registers



- (1) Assertion of $\overline{\text{FAULT}}$ occurs if $\text{FLTEN} = 1$.
- (2) Disabling of pre-driver occurs if $\text{SDNEN} = 1$.

Figure 9. FLGFLG and FLGLATCH_EN

CSCFG (address 0x0A): Current Sense Configuration Register

Bit	Name	Type ⁽¹⁾	Reset	Description
7:3	RSVD	R	0000 0	Reserved
2:0	CSOFFSET	RW	000	Current-sense offset 000: 0.5 V 001: 1 V 010: 1.5 V Others: 0.5 V

- (1) R: Read W: Write

PDCFG (address 0x0B): Pre-Driver Configuration Register

Bit	Name	Type ⁽¹⁾	Reset	Description
7:2	RSVD	R	0000 00	Reserved
1:0	DEADT	RW	00	Dead time (= t_{dead}) 00: 2.1 μs 01: 1.6 μs 10: 1.1 μs 11: 0.6 μs The actual dead time has $\pm 0.1\text{-}\mu\text{s}$ variation from the typical value.

- (1) R: Read W: Write

DIAG (address 0x0C): Diagnosis Register

Bit	Name	Type	Reset	Description
7:3	RSVD	R	0000 0	Reserved
2	VCCUVRST	R	0	nRES reset source information
1	WDTRST	R	0	Bit 2 = VCCUVRST - VCC undervoltage
0	CMRST	R	0	Bit 1 = WDTRST - watchdog timer Bit 0 = CMRST - clock monitor 0: Read = Reset has not occurred.

Bit	Name	Type	Reset	Description
				Write = No effect 1: Read = A corresponding reset source caused the last reset condition. Write = No effect Read access to this register clears the bits.

SPARE (address 0x0D): Spare Register

Bit	Name	Type ⁽¹⁾	Reset	Description
7:2	SPARE	RW	0000 00	Spare registers for future use. Read and write have no effect.
1:0	SEL_COMP_HYS	RW	00	Select phase comparator hysteresis voltage. The following show the typical values. 00: 0 V 01: 25 mV 10: 50 mV 11: 100 mV

(1) R: Read W: Write

Charge Pump

Description:

The charge-pump block generates a supply for the high-side and low-side pre-drivers to maintain the gate voltage on the external FETs. Use of an external storage capacitor (CCP) and bucket capacitors (C1, C2) supports pre-driver slope and switching-frequency requirements. R1 and R2 reduce switching current if required. The charge pump has voltage-supervisor functions such as over- and undervoltage, and selectable stop conditions for pre-drivers.

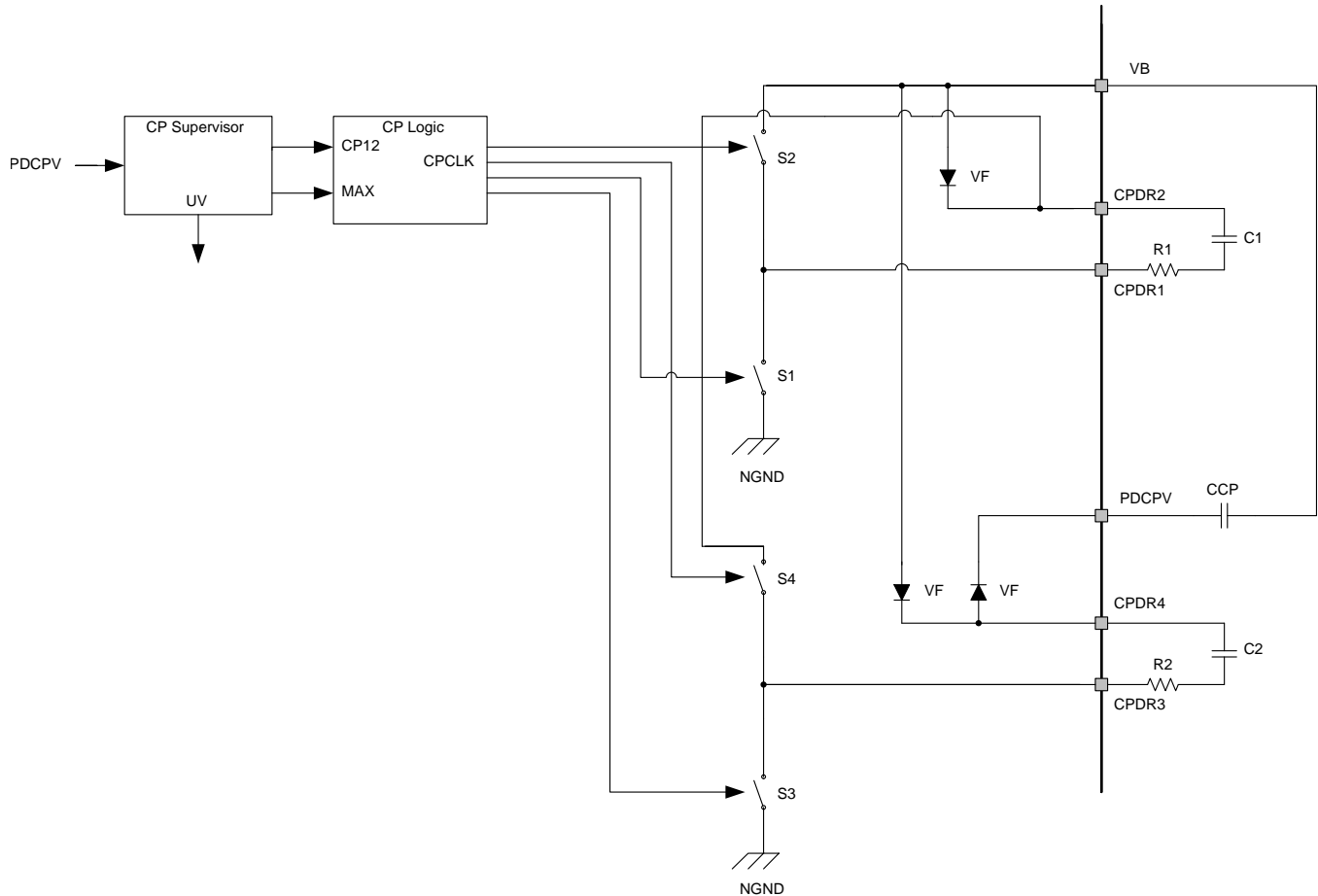


Figure 10. Charge-Pump Block Diagram

Table 5. Charge-Pump Electrical Characteristics

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
VB = 12 V, TA = -40°C to +150°C (unless otherwise specified)					
CHARGE PUMP					
Vchv1_0	Output voltage, PDCPV	VB + 7	VB + 8	-	V
Vchv1_1	Output voltage, PDCPV	VB + 5.5	VB + 6.5	-	V
Vchv1_2	Output voltage, PDCPV	VB + 4.5	VB + 5.5	-	V
Vchv2_0	Output voltage, PDCPV	VB + 10	VB + 12	VB + 14	V
Vchv2_1	Output voltage, PDCPV	VB + 9.5	VB + 11.5	VB + 13.5	V

Table 5. Charge-Pump Electrical Characteristics (continued)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
Vchv2_2	Output voltage, PDCPV	VB = 12 V, load = 18 mA, C1 = C2 = 47 nF, CCP = 2.2 μ F, R1 = R2 = 0 Ω	VB + 9	VB + 11	VB + 13	V
Vchv3_0	Output voltage, PDCPV	VB = 18 V, load = 0 mA, C1 = C2 = 47 nF, CCP = 2.2 μ F, R1 = R2 = 0 Ω	VB + 10	VB + 12	VB + 14	V
Vchv3_1	Output voltage, PDCPV	VB = 18 V, load = 13 mA, C1 = C2 = 47 nF, CCP = 2.2 μ F, R1 = R2 = 0 Ω	VB + 10	VB + 12	VB + 14	V
Vchv3_2	Output voltage, PDCPV	VB = 18 V, load = 22 mA, C1 = C2 = 47 nF, CCP = 2.2 μ F, R1 = R2 = 0 Ω	VB + 10	VB + 12	VB + 14	V
VchvOV	Overvoltage detection threshold		35	37.5	40	V
VchvUV	Undervoltage detection threshold		VB + 4	VB + 4.5	VB + 5	V
t _{chv} ⁽¹⁾	Rise time	VB = 5.3 V, C1 = C2 = 47 nF, CCP = 2.2 μ F, R1 = R2 = 0 Ω , Vchv, UV released		1	2	ms
Ron	On-resistance, S1-S4	See Figure 10		8		Ω

(1) Specified by design.

Pre-Driver

Description:

The pre-driver block provides three high-side pre-drivers and three low-side pre-drivers to drive external N-channel MOSFETs. The turnon side of the high-side pre-drivers supplies the large N-channel transistor current for quick charge, and PMOS supports output voltages up to PDCPV. The turnoff side of the high-side pre-drivers supplies the large N-channel transistor current for quick discharge. The low-side pre-drivers supply the large N-channel transistor current for charge and discharge. VCP12 (created by a charge pump) controls the output voltage of the low-side pre-driver to output less than 18 V. The pre-driver has a stop condition in some fault conditions ([Fault Detection](#)) and SPI set ([Serial Port I/F](#)).

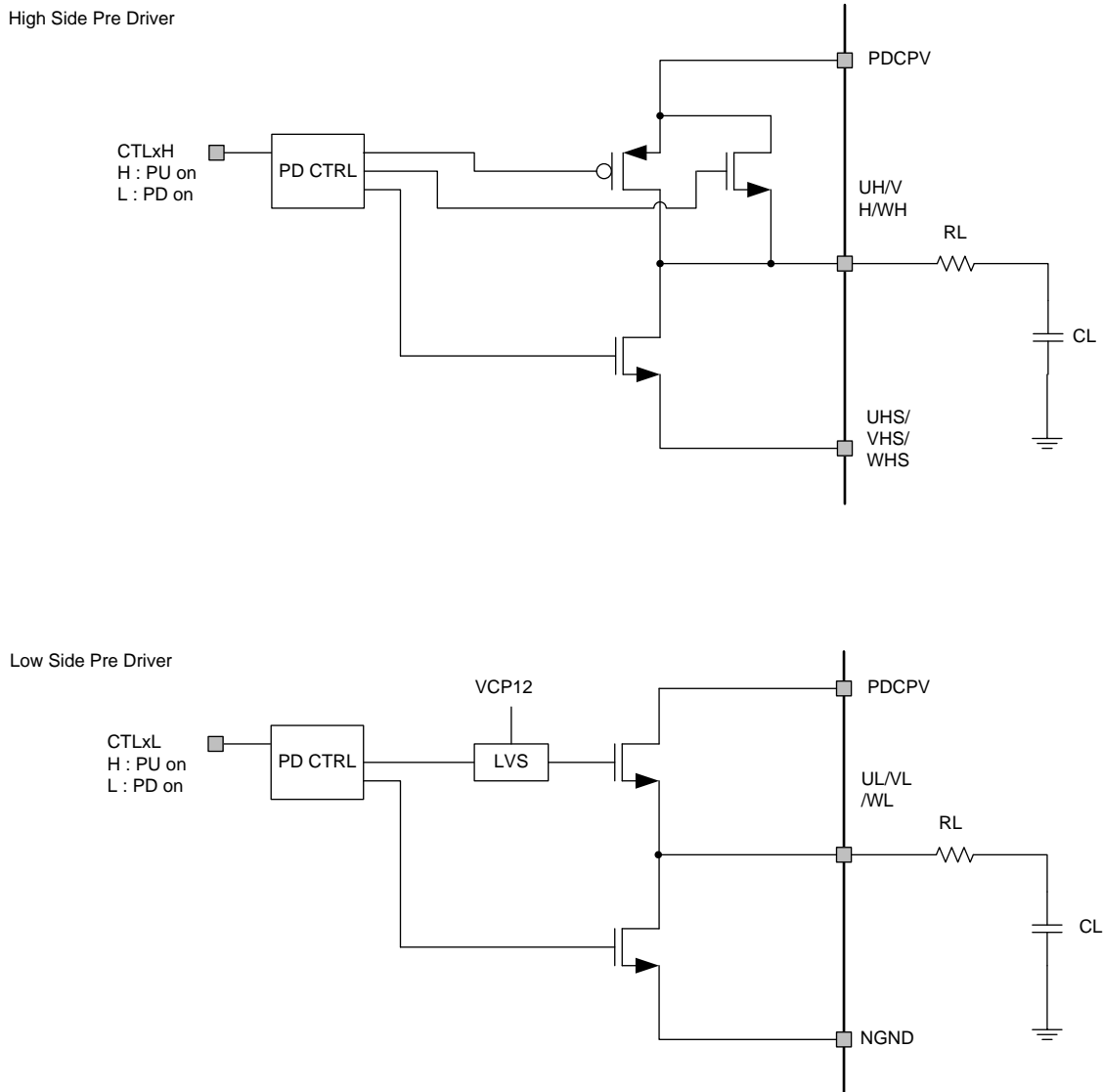
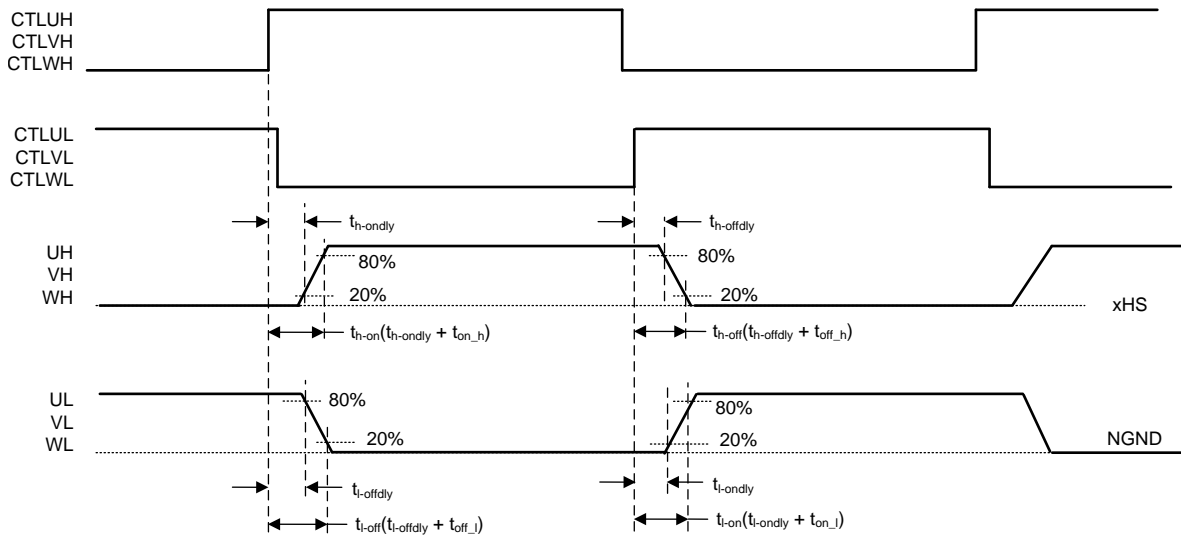


Figure 11. Pre-Driver Block Diagram

Table 6. Pre-Driver Electrical Characteristics

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
VB = 12 V unless otherwise stated, TA = -40°C to +150°C, unless otherwise specified						
HIGH-SIDE PRE-DRIVER						
VOH_H	Output voltage, turnon side	Isink = 10 mA, PDCPV - xH		1.35	2.7	V
VOL_H	Output voltage, turnoff side	Isource = 10 mA, xH - xHS		25	50	mV
RONH_HP	On-resistance, turnon side (Pch)	U(V/W)H = PDCPV - 1 V		135	300	Ω
RONH_HN	On-resistance, turnon side (Nch)	U(V/W)H = PDCPV - 2.5 V		4	8	Ω
RONL_H	On-resistance turnoff side			2.5	5	Ω
t _{on_h} ⁽¹⁾	Turnon time	C _L = 12 nF, R _L = 0 Ω from 20% to 80%	50	-	200	ns
t _{off_h} ⁽¹⁾	Turnoff time	C _L = 12 nF, R _L = 0 Ω from 80% to 20%	50	-	200	ns
t _{h-ondly} ⁽¹⁾	Output delay time	C _L = 12 nF, R _L = 0 Ω to 20%, no dead time	-	200	-	ns
t _{h-offdly} ⁽¹⁾	Output delay time	C _L = 12 nF, R _L = 0 Ω to 80%, no dead time	-	200	-	ns
VGS_hs	Gate-source high -side voltage difference	xH-xHS	-0.3		18	V
LOW-SIDE PRE-DRIVER						
VOH_L1	Output voltage, turnon side	VB = 12 V, Isink = 10 mA, xL -NGND	10	12	14	V
VOH_L2	Output voltage, turnon side	VB = 5.3 V, Isink = 10 mA, xL - NGND	5.5	7.5	10	V
VOL_L	Output voltage, turnoff side	Isource = 10 mA, xL - NGND	-	25	60	mV
RONH_L	On-resistance, turnon side		-	6	12	Ω
RONL_L	On-resistance, turnoff side			2.5	6	Ω
t _{on_l} ⁽¹⁾	Turnon time	C _L = 18 nF, R _L = 0 Ω, from 20% to 80% of 12 V, from 20% to 80% of 6 V (VB = 5.3 V)	50	-	200	ns
t _{off_l} ⁽¹⁾	Turnoff time	C _L = 18 nF, R _L = 0 Ω, from 80% to 20% of 12 V, from 80% to 20% of 6 V (VB = 5.3 V)	50	-	200	ns
t _{l-ondly} ⁽¹⁾	Output delay time	C _L = 18 nF, R _L = 0 Ω, to 20% of 12 V, to 20% of V _{OH} = 6 V (VB = 5.3 V), no dead time	-	200	-	ns
t _{l-offdly} ⁽¹⁾	Output delay time	C _L = 18 nF, R _L = 0 Ω, to 80% of 12 V, to 80% of V _{OH} = 6 V (VB = 5.3 V), no dead time	-	200	-	ns
t _{diff1} ⁽¹⁾	Differential time1	(Th-on) - (Tl-off), no dead time, See Figure 12	-200	0	200	ns
t _{diff2} ⁽¹⁾	Differential time2	(Tl-on) - (Tl-off), no dead time, See Figure 12	-200	0	200	ns
t _{dead} ⁽¹⁾	Dead time	OSC1 = 10 MHz SPI register PDCFG.DEADT	2 1.5 1 0.5		2.2 1.7 1.2 0.7	μs

(1) Specified by design.



NOTE: This diagram excludes dead time to explain the timing parameters of the pre-driver.

Figure 12. Delay Time From Input to Output

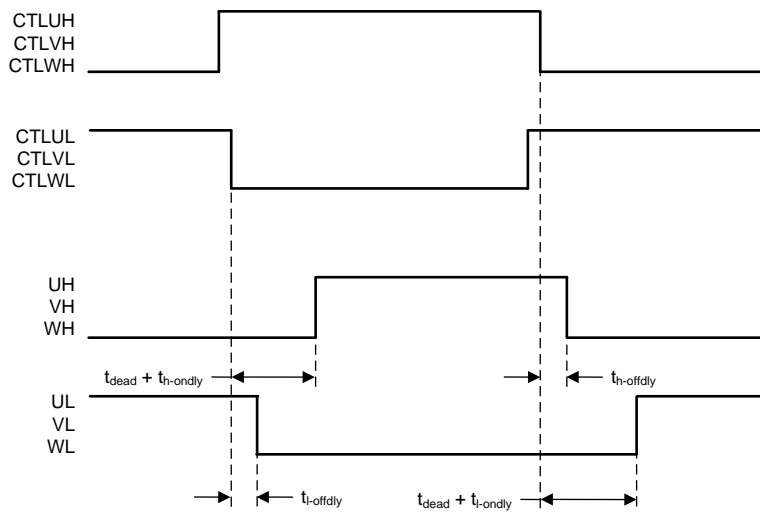


Figure 13. Dead Time

Phase Comparator

Description:

The three-channel comparator module monitors the external FETs by detecting the drain-source voltage across the high-side and low-side FETs. PHTM is the threshold level of the comparators usable for sensorless communication. Figure 14 shows an example of the threshold level.

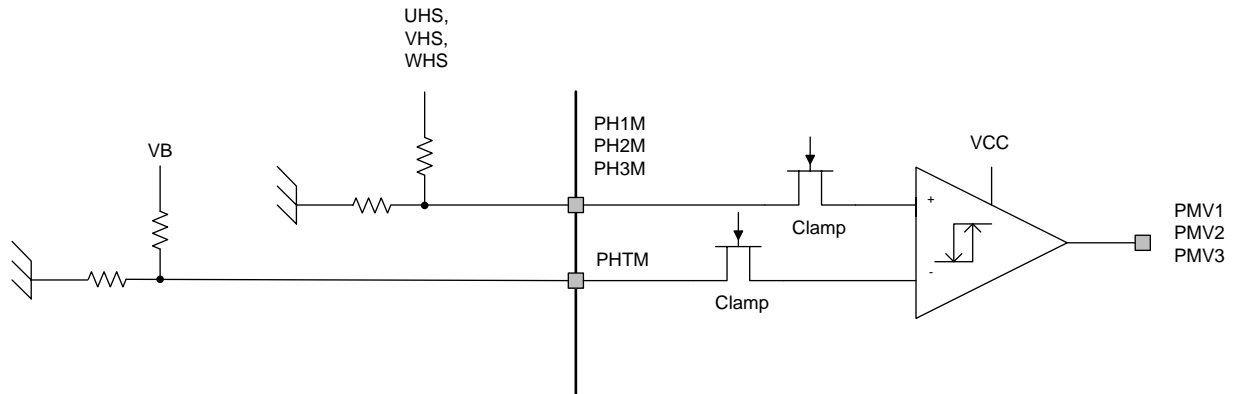


Figure 14. Phase Comparator Block Diagram

Table 7. Phase Comparator Electrical Characteristics

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS		
VB = 12 V, TA = -40°C to +150°C (unless otherwise specified)							
PHASE COMPARTOR							
V _{IOfs}	Input offset voltage	-15	-	15	mV		
V _{Im1}	Input voltage range, PHTM	VB = 6 V – 26.5 V		4.5	V		
V _{Im2}	Input voltage range, PHTM	VB = 5.3 V		4.2	V		
V _{Ip}	Input voltage range, PHxM	-1	-	VB	V		
V _{hys}	Threshold hysteresis voltage	SPI register SPARE. SEL_COMP_HYS		-	-	mV	
				12.5	25		50
				25	50		100
				50	100		200
V _{OH}	Output high voltage	I _{sink} = 2.5 mA		0.9 × VCC	V		
V _{OL}	Output low voltage	I _{source} = 2.5 mA		0.1 × VCC	V		
t _{res_tr} ⁽¹⁾	Response time, rising	C _L = 100 pF		0.7	1.5	μs	
t _{res_tf} ⁽¹⁾	Response time, falling	C _L = 100 pF		0.7	1.5	μs	

(1) Specified by design.

Motor-Current Sense

Description:

The operational amplifier operates with an external resistor network for higher flexibility to adjust the current measurement to application requirements. The first-stage amplifier operates with the external resistor and the output voltage up to V_B at ALFB. External resistors adjust the amplifier gain by 10 to 30 times. The second-stage amplifier is buffered to MCU at ALV. The current sense has a comparator for motor overcurrent (OVAD). ADTH is the overcurrent threshold level and is the value set by SPI. Figure 15 shows the curve of detection level. ALFB is divided by 2. Compare this value with ADTH. In recommended application, the zero-point adjustment is required as large error offset in initial condition.

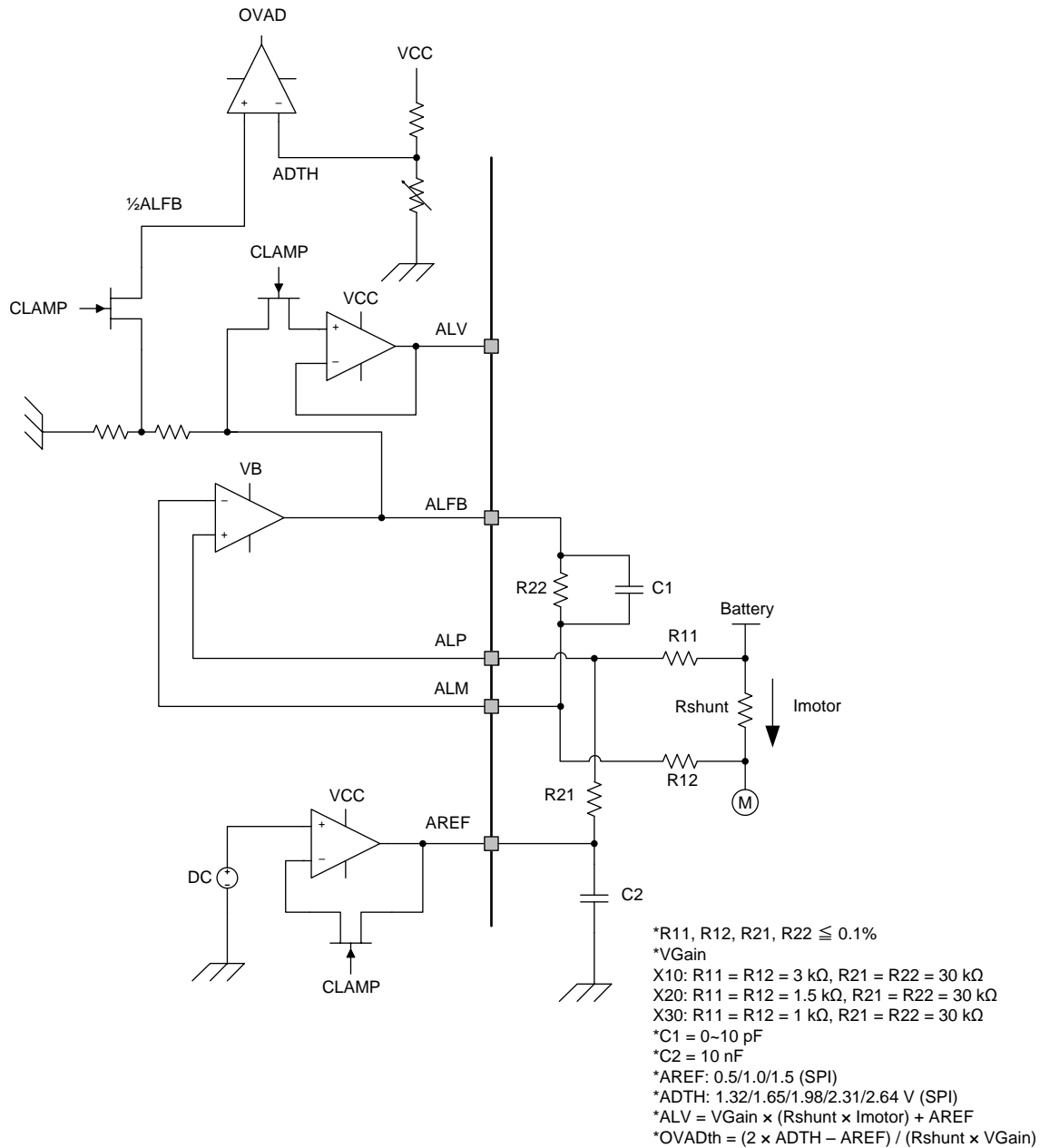


Figure 15. Motor Current-Sense Block Diagram

Table 8. Motor Current-Sense Electrical Characteristics

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
VB = 12 V, TA = -40°C to +150°C (unless otherwise specified)						
MOTOR CURRENT SENSE						
VOfs	Input offset voltage		-5		5	mV
VO_0	Output voltage, ALV	Imotor = 0 A, SPI register CSCCFG. CSOFFSET	-	0.5 1 1.5	-	V
VLine	Linearity, ALV	Rshunt = 1 mΩ, R11 = R12 = 1 kΩ, R21 = R22 = 30 kΩ	29.4	30	30.6	mV/A
VGain	Gain		10	30	-	V/V
Tset_TR1 ⁽¹⁾	Settling time (rise), ALV ±1%	Rshunt = 1 mΩ, VGain = 30, CL = 100 pF, Imotor = 0 A → 30 A, (ALV: 1 V → 1.9 V, AREF = 1 V)	-	1	2.5	μs
Tset_TR2 ⁽¹⁾	Settling time(rise), ALV ±1%	Rshunt = 1 mΩ, VGain = 30, CL = 100 pF, Imotor = 0 A → 60 A, (ALV: 1 V → 2.8 V, AREF = 1 V)	-	1	2.5	μs
Tset_TF1 ⁽¹⁾	Settling time(fall), ALV ±1%	Rshunt = 1 mΩ, VGain = 30, CL = 100 pF, Imotor = 30 A → 0, (ALV: 1.9 V → 1 V, AREF = 1 V)	-	1	2.5	μs
Tset_TF2 ⁽¹⁾	Settling time(fall), ALV ±1%	Rshunt = 1 mΩ, VGain = 30, CL = 100 pF, Imotor = 60 A → 0, (ALV: 2.8 V → 1 V, AREF = 1 V)	-	1	2.5	μs
OVADth	Overcurrent threshold	Rshunt = 1 mΩ, VGain = 30, AREF = 1 V, ADTH = 1.98 V, SPI register FLTCFG. MTOCTH, OVADth = (2 × ADTH -- AREF) / (Rshunt × VGain)	89.1	99	108.9	A
TDEL_OVAD ⁽¹⁾	Propagation delay (rise or fall)		-	-	1.5	μs
tfiltMTOC	filtering time	OSC1 = 9 MHz-11 MHz	0.8	1	1.2	μs

(1) Specified by design.

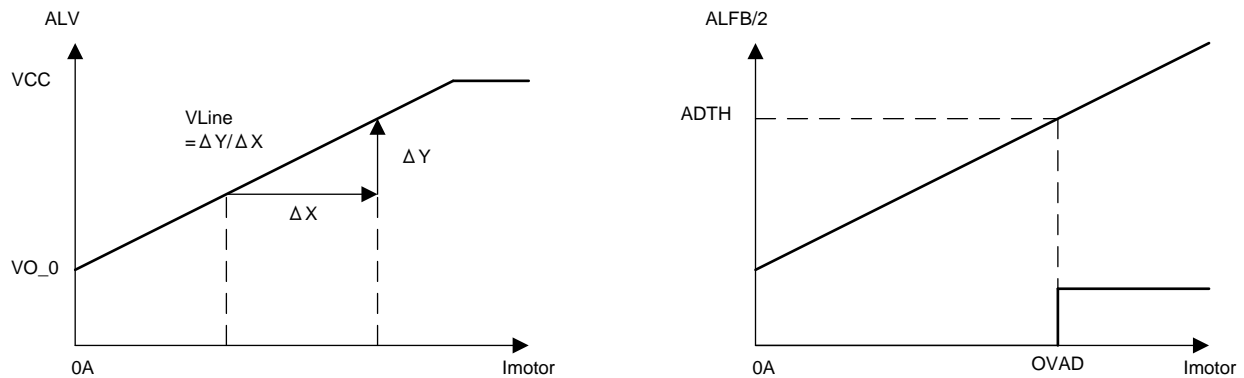
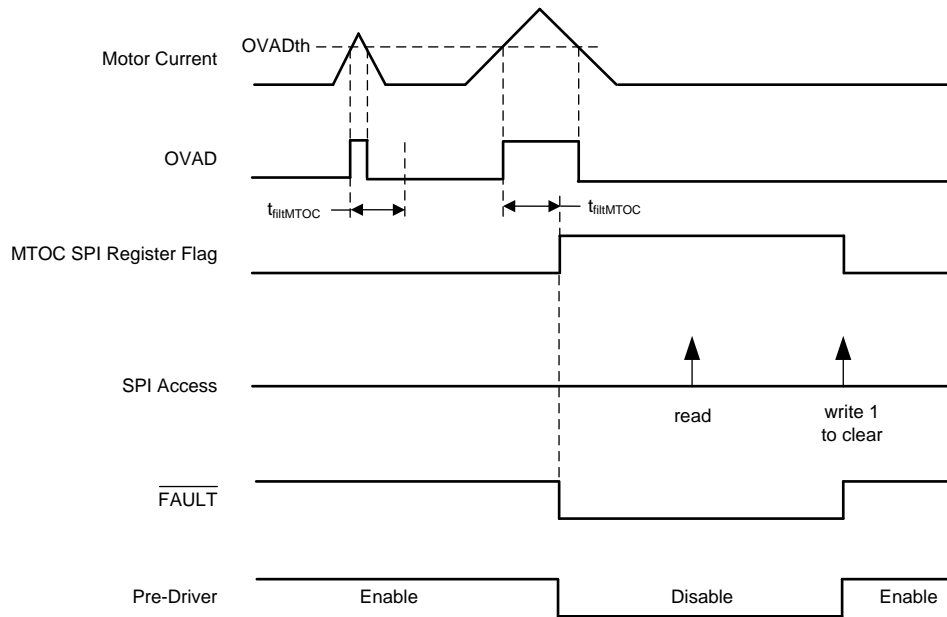


Figure 16. Motor Current Sense and Overcurrent



- (1) MCU must set the FLTCFG.FLGLATCH_EN bit to 1 to get the latch-type operation shown in this figure.
- (2) When MTOC condition is detected, \overline{FAULT} is asserted to low if FE_MTOC bit is 1.
- (3) When MTOC condition is detected, Pre Driver is disabled if SE_MTOC is 1.

Figure 17. Motor Overcurrent Event

Regulators

Description:

The regulator block offers 3.3-V LDOs. The VCC LDO regulates VB down to 3.3 V with an external PNP controlled by the regulator block. This 3.3-V LDO is supplied to MCU and other components.

The VDD regulator regulates VB down to 3.3 V with internal FET and controller. The 3.3-V LDO with the external PNP is protected against short to GND fault. Overvoltage and undervoltage events of both supplies are detected. The under voltage of the 3.3-V LDO with the external PNP is set by SPI.

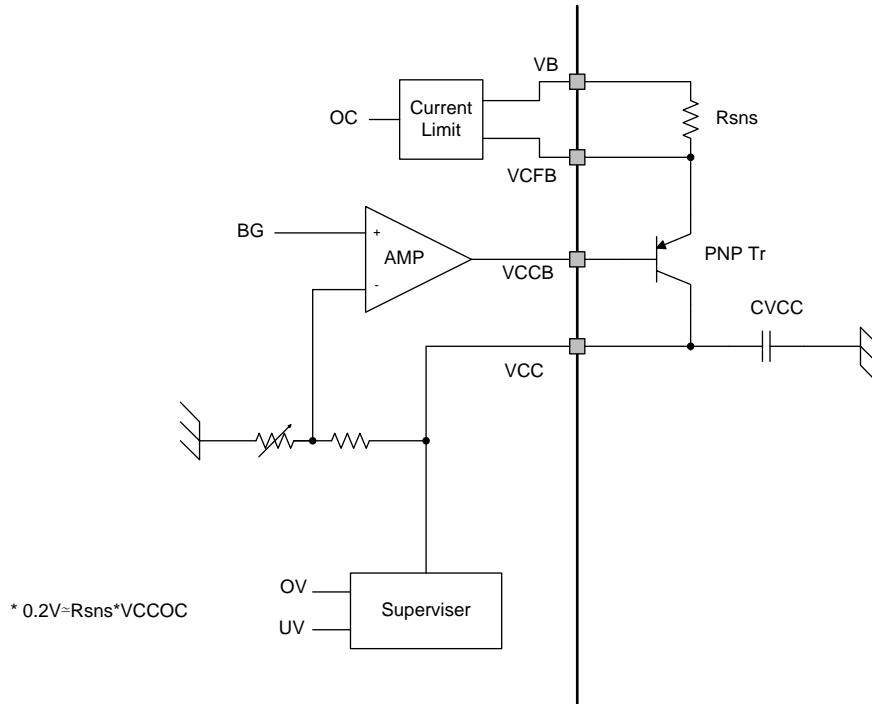


Figure 18. VCC Block Diagram (External Driver)

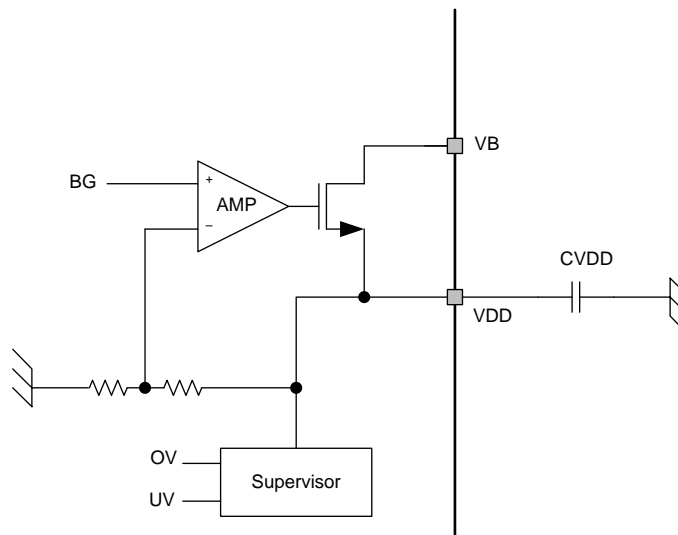


Figure 19. VDD Block Diagram

Table 9. VCC and VDD Electrical Characteristics

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
VB = 12 V, T_A = –40°C to +150°C (unless otherwise specified)						
VCC						
VCC1	Output Voltage		3.23	3.3	3.37	V
IBVCC	Base Current		2			mA
hfePNP	DC current gain of external PNP		100	-	-	
VLRVCC	Load regulation	ILVCC = 5 mA to 200 mA	-20	-	20	mV
CVCC	External Capacitance		22		100	μF
RVCC	ESR of external Capacitor				300	mΩ
VCCUV	Under voltage detection threshold	SPI register FLTCFG. VCCUVTH	2 2.2	2.2 2.4	2.4 2.6	V
VCCUVHYS	Under voltage detection threshold hysteresis		33	66	132	mV
VCCOV	Overvoltage detection threshold		3.5	3.8	4.1	V
VCCOC	Current Limit	$R_{sns} = 0.51 \Omega, 0.2 V = R_{sns}^{(1)} \times VCCOC$	300	400	550	mA
T _{vcc1} ⁽²⁾	Rise Time	VCC > VCCUV, CVCC = 22 μF			0.5	ms
T _{vcc2} ⁽²⁾	Rise Time	VCC > VCCUV, CVCC = 100 μF			1.5	ms
VDD						
VDD	Output Voltage		3	3.3	3.6	V
CVDD	Load Capacitance			1		μF
VDDUV	Under voltage detection threshold		2.1	2.3	2.5	V
VDDOV	Overvoltage detection threshold		4	4.3	4.6	V
T _{vdd} ⁽²⁾	Rise Time	VDD > VDDUV, CVDD = 1 μF			100	μs

(1) No variation of the external components

(2) Specified by design.

VB Monitor

Description:

The VB monitoring system has two comparators for under- and overvoltage, and has pre-driver stop-controlling system. Overvoltage provides a selectable pre-driver stop condition (SPI control), while undervoltage must stop pre-driver operation under detection (no selectable). The system should return to normal operation automatically after undetected level.

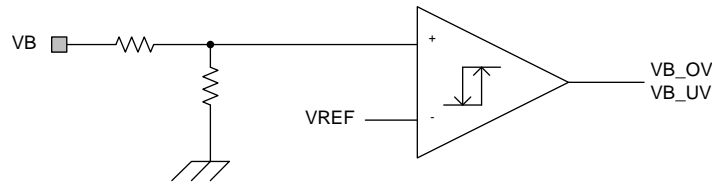


Figure 20. VB Monitor Block Diagram

Table 10. Electrical Characteristics

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
VB = 12 V, T _A = -40°C to +150°C (unless otherwise specified)						
VB MONITOR						
VBOV	VB overvoltage detection threshold level		26.5	27.5	28.5	V
VBUV	VB Undervoltage detection threshold level	SPI register FLTCFG.VBUVTH	3.65	4	4.35	V
			4.15	4.5	4.85	
			4.65	5	5.35	
			5.15	5.5	5.85	

Thermal Shut Down

Description:

The device has temperature sensors that produce pre-driver stop condition if the chip temperature exceeds 175°C.

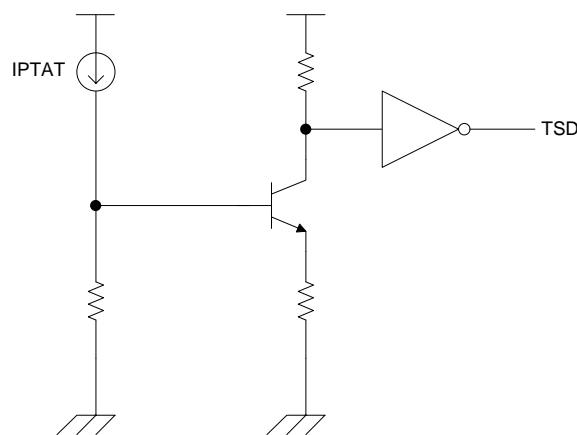


Figure 21. Thermal Shutdown Block Diagram

Table 11. Electrical Characteristics

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
VB = 12 V, TA = -40°C to +150°C (unless otherwise specified)						
THERMAL SHUT DOWN						
TSD ⁽¹⁾	Thermal shut down threshold level		155	175	195	°C
TSDhys ⁽¹⁾	Thermal shut down hysteresis		5	10	15	°C

(1) Specified by design

Oscillator

Description:

The oscillator block generates two 10-MHZ clock signals. OSC1 is the primary clock used for internal logic-synchronization and timing control. OSC2 is the secondary clock used to monitor the status of OSC1.

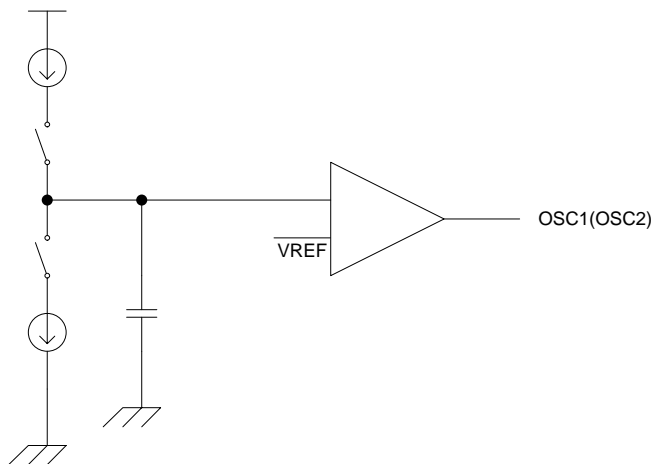
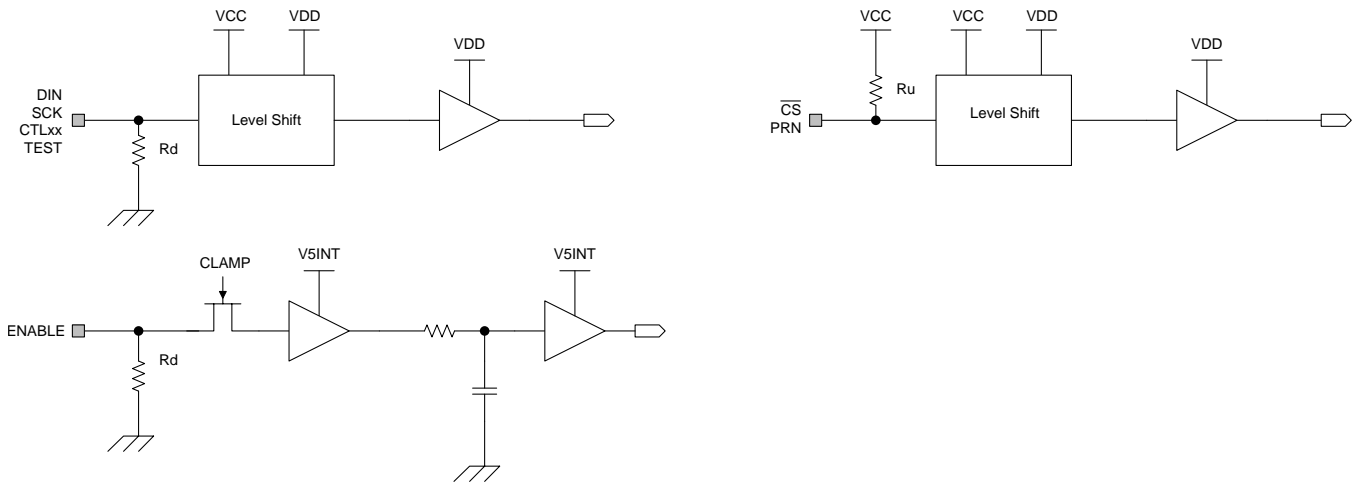


Figure 22. Oscillator Block Diagram

Table 12. Oscillator Electrical Characteristics

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
VB = 12 V, TA = -40°C to +150°C (unless otherwise specified)						
OSCILLATOR						
OSC1	OSC1 frequency		9	10	11	MHz
OSC2	OSC2 frequency			10		MHz

I/O



* V5INT is the internal power supply.

Figure 23. Input Buffer1 Block Diagram

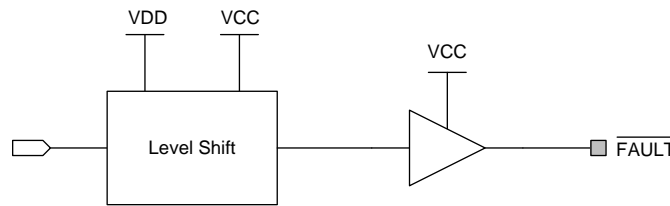


Figure 24. Output Buffer1 Block Diagram

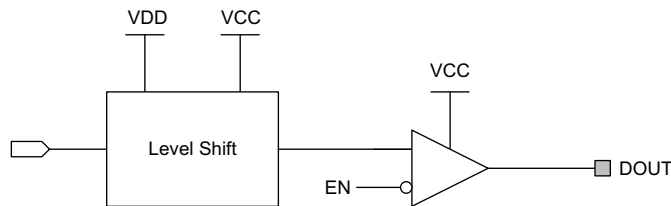


Figure 25. Output Buffer2 Block Diagram

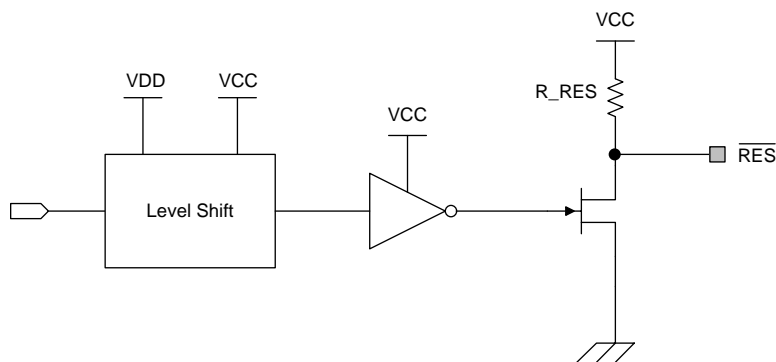


Figure 26. Output Buffer3 Block Diagram

Table 13. Electrical Characteristics

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
VB = 12 V, TA = -40°C to +150°C (unless otherwise specified)						
Input Buffer1						
V _{IH}	Input threshold logic high	0.7 × VCC			V	
V _{IL}	Input threshold logic low	0.3 × VCC			V	
R _u or R _d	Input pullup or pulldown resistance	50	100	150	kΩ	
Output Buffer1(2)						
V _{OH}	Output level logic high	Isink = 1 mA			0.9 × VCC	V
V _{OL}	Output level logic low	Isource = 1 mA			0.1 × VCC	V
Output Buffer3						
R _{RES}	Pull up Resistor	2	3	4	kΩ	
V _{OL}	Output level logic low	Isource = 2 mA			0.1 × VCC	V

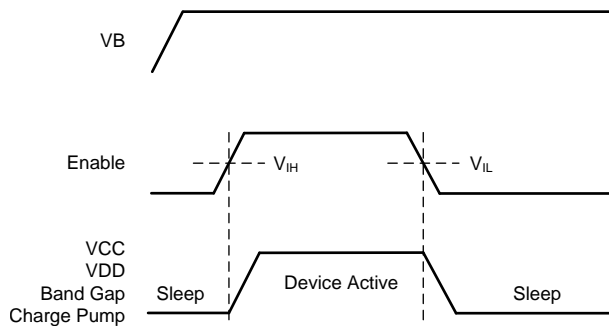


Figure 27. ENABLE Timing Chart

Table 14. Recommended Pin Termination

PIN NAME	DESCRIPTION	TERMINATION
TEST	Test mode input	OPEN

Fault Detection

Table 15. Fault Detection

ITEMS	SPI FLTFLG	Pre Driver ⁽¹⁾	FAULT ⁽²⁾	RES	Others
VB - Overvoltage	VBOV	Disable	L	H	
VB - Undervoltage	VBUV	Disable	L	H	
CP - Overvoltage	CPOV	Disable	L	H	
CP - Undervoltage	CPUV	Disable	L	H	
VCC - Overvoltage	VCCOV	Disable	L	H	
VCC - Under Voltage	-	Disable ⁽³⁾	H	L	
VCC - Overcurrent	VCCOC	Disable	L	H	
Motor - Overcurrent	MTOC	Disable	L	H	
VDD - Overvoltage	VDDOV	Disable	L	H	
VDD - Undervoltage	-	Disable ⁽³⁾	H	L	
Thermal shutdown	TSD	Disable	L	H	
Watch Dog	-	-	H	L	
Clock Monitor	-	-	H	L	

(1) Pre-driver is disabled if the conditions occur and SDNEN register bits are 1.

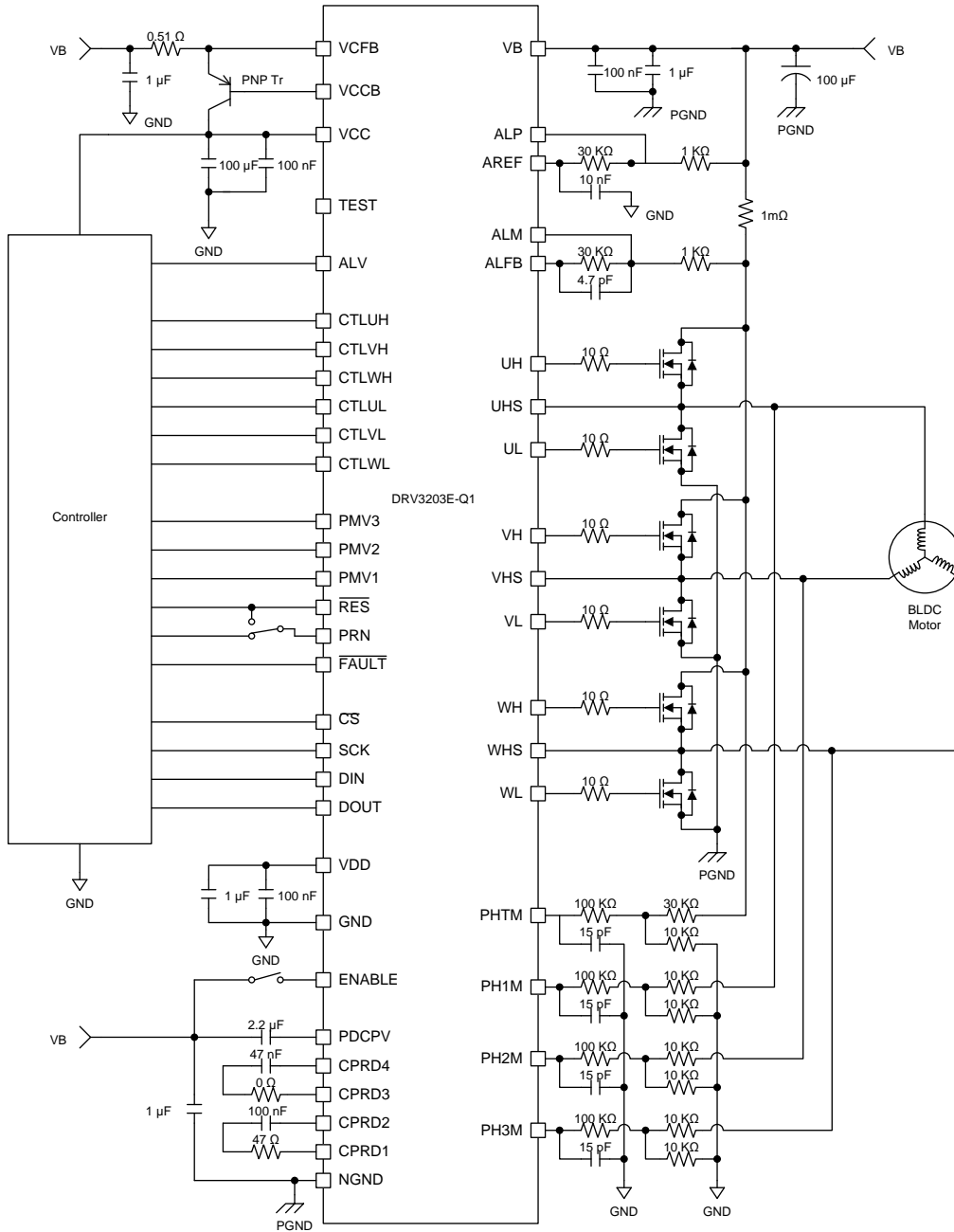
(2) FAULT pin is asserted to low if the conditions occur and FLTEN register bits are 1.

(3) Pre-driver is disabled by VCC undervoltage and VDD undervoltage conditions regardless of SPI register setting.

Table 15. Fault Detection (continued)

ITEMS	SPI FLTLFG	Pre Driver ⁽¹⁾	FAULT ⁽²⁾	RES	Others
SPI format error	-	-	H	H	SPI serial out error bit

Application Description



修订历史记录

Changes from Original (November 2013) to Revision A	Page
• Changed symbol for the Data delay time, SCK to DOUT parameter in the <i>SPI ELECTRICAL CHARACTERISTICS</i> table from t_v to t_d	9
• Changed the delay time, SCK to DOUT image reference from Figure 6 to Figure 5 in the <i>SPI ELECTRICAL CHARACTERISTICS</i> table	9
• Added ADTH to the bit 6:4 description in the FLTCFG register table	11
• Changed the description for writing a 0 to bit 2 in the FLTCFB register table from 2.3 to 2.2 V	11
• Changed the dead time description for bit 1:0 in the PDCFG register table from 2, 1.5, 1, and 0.5 to 2.1, 1.6, 1.1, and 0.6 (respectively). Also changed the actual deadtime from ± 0.2 to ± 0.1	15
• Changed the max value for the RONH_HP parameter from 310 to 300 in the <i>Pre-Driver Electrical Characteristics</i> table	20
• Deleted the 1 from the symbols for the time parameters (t_{on_h} , t_{off_h} , t_{h-on} , and t_{h-off}) for the high-side pre-driver in the <i>Pre-Driver Electrical Characteristics</i> table	20
• Changed the max for the VOL_L parameter from 55 to 60 in the <i>Pre-Driver Electrical Characteristics</i> table	20
• Changed the max for the RONL_L parameter from 5 to 6 in the <i>Pre-Driver Electrical Characteristics</i> table	20
• Changed the symbol for the turnoff time parameter for the low-side pre-driver from t_{off_h} to t_{off_l} in the <i>Pre-Driver Electrical Characteristics</i> table	20
• Changed conditions of Tset_TR2, Tset_TF2 and OVADth in the <i>Motor Current-Sense Electrical Characteristics</i> table ..	24
• Changed the value for the VCCUVHYS parameters in the <i>VCC and VDD Electrical Characteristics</i> table from 50, 100, and 200 to 33, 66, and 132	27

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
DRV3203EPHPRQ1	OBSOLETE	HTQFP	PHP	48		TBD	Call TI	Call TI		DRV3203E	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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GENERIC PACKAGE VIEW

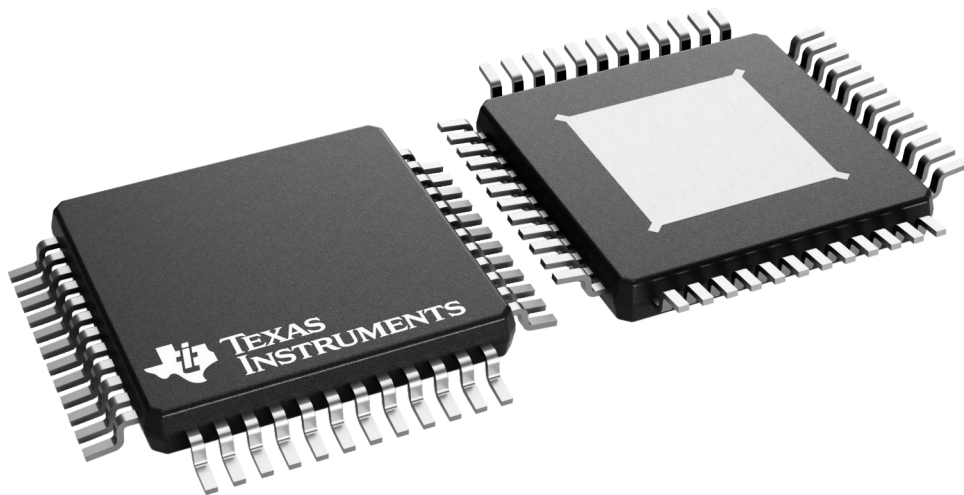
PHP 48

TQFP - 1.2 mm max height

7 x 7, 0.5 mm pitch

QUAD FLATPACK

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4226443/A

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